

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for the application of a gating signal in [[a]] an insulated double gate FET, which comprises applying, in response to a first signal fed into a first gate electrode, a second signal that has a same signal-level temporal-change direction and a same signal amplitude as the first signal and has a signal level shifted by a predetermined magnitude to a second gate electrode.

Claim 2 (Currently Amended): A method for the application of a gating signal in [[a]] an insulated double gate FET, which comprises applying, in response to a first signal fed into a first gate electrode, a second signal that has a same signal-level temporal-change direction and a same signal amplitude as the first signal and has a slower or faster rise time or [[a]] fall time to a second gate electrode.

Claim 3 (Currently Amended): A method for the application of [[a]] an insulated gating signal in a double gate FET, which comprises applying, in response to a first signal fed into a first gate electrode, a second signal that has a same signal-level temporal-change direction and a same signal amplitude as the first signal and has a predetermined time difference to a second gate electrode.

Claim 4 (Currently Amended): An integrating circuit furnished with [[a]] an insulated double gate FET utilizing the method for the application of a gating signal set forth in any one of claims 1 to 3.